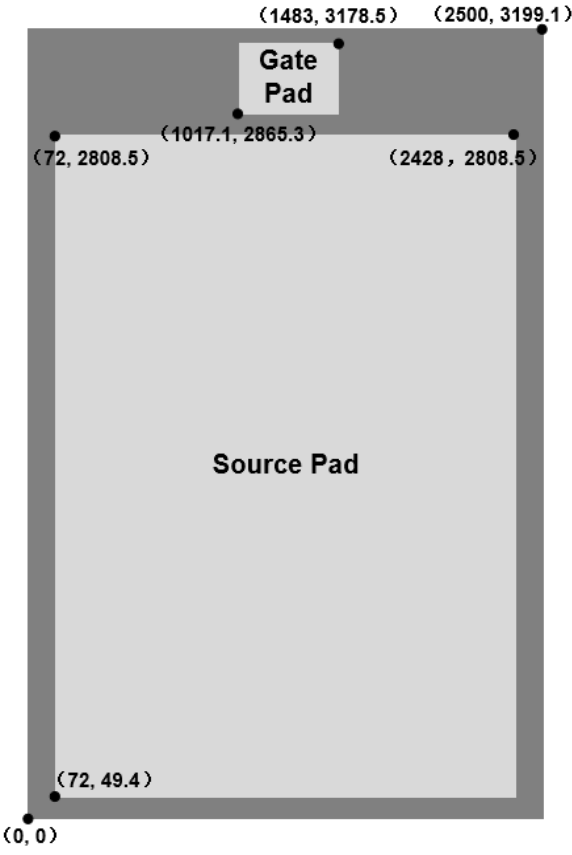


Features

- 120V, 9.0mΩ typ., 75A, N-channel SGT MOSFET
- High-Frequency Switching and Synchronous Rectification in SMPS
- DC/DC in Telecoms and Industrial

Wafer Information

Chip drawing	Parameter	Value	Unit
	Wafer Size	200	mm
	Wafer Thickness	200	μm
	Chip Size	2560*3259.1	μm*μm
	Scribe Line Size	60	μm
	Gate Pad Size	465.9* 313.2	μm
	Source Pad Size	2356*2759.1	μm*μm
	Gross Die	3400	
	Front Metal (AlCu)	4	μm
	Back Metal (Ti/Ni/Ag)	1 / 3 / 10	KA
	Top passivation (TEOS/SiN)	3 / 7	KA

1 Absolute Characteristics

($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified, PDFN5*6 Package Reference)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	120	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	75	A

2 Electrical characteristics

($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified, PDFN5*6 Package Reference)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	120			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 120\text{ V}$, $T_C = 25\text{ }^{\circ}\text{C}$			1	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$		7.0	9.0	m Ω

Note

1. Product must be handled only at ESD safe workstations. Standard ESD precautions and safe work environments are as defined in MIL-HDBK-263.
2. Product must be handled only in a class 10,000 or better-designated clean room environment.
3. Proper storage conditions are necessary to prevent product contamination and/or degradation after shipment.
4. Cool Semiconductor reserves the right to modify the datasheet. Customer should get the latest specification before placing orders. If you have any questions, you can contact us to confirm.